

# Hyeong Joon Kim

## List of Publications by Year in descending order

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191  
papers

4,073  
citations

101384

36  
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168136

53  
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192  
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192  
docs citations

192  
times ranked

3797  
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#	ARTICLE	IF	CITATIONS
1	Effect of sweeping direction on the capacitance-voltage behavior of sputtered SiO <sub>2</sub> /4H-SiC metal-oxide semiconductors after nitric oxide post-deposition annealing. <i>Physica Scripta</i> , 2019, 94, 125811.	1.2	3
2	Densification of silicon dioxide formed by plasma-enhanced atomic layer deposition on 4H-silicon carbide using argon post-deposition annealing. <i>Ceramics International</i> , 2018, 44, 13565-13571.	2.3	7
3	Effects of post-deposition annealing on sputtered SiO <sub>2</sub> /4H-SiC metal-oxide-semiconductor. <i>Solid-State Electronics</i> , 2018, 139, 115-120.	0.8	7
4	On-axis Si-face 4H-SiC epitaxial growth with enhanced polytype stability by controlling micro-steps during the H <sub>2</sub> etching process. <i>CrystEngComm</i> , 2017, 19, 2359-2366.	1.3	4
5	Impact of an Interfacial Layer on the Electrical Performance of n-Channel Tin Monoxide Field-Effect Transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1700213.	1.2	5
6	Oxygen- and photoresist-related interface states of 4H-SiC Schottky diode observed by deep-level transient spectroscopy. <i>Journal of Applied Physics</i> , 2017, 122, 094504.	1.1	4
7	Low-Temperature Fabrication of Amorphous Zinc-Tin-Oxide Thin Film Transistors with In-Situ Annealing Process. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P728-P732.	0.9	2
8	Analysis of the threshold switching mechanism of a Te-SbO selector device for crosspoint nonvolatile memory applications. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	12
9	Composition-dependent structural and electrical properties of p-type SnO <sub>x</sub> thin films prepared by reactive DC magnetron sputtering: effects of oxygen pressure and heat treatment. <i>RSC Advances</i> , 2016, 6, 71757-71766.	1.7	21
10	Impact of thermal oxidation pressure and temperature on deactivation of the interfacial trap states in Al <sub>2</sub> O <sub>3</sub> /GaAs MOS capacitor. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 1911-1915.	0.8	1
11	Comparative Study of 4H-SiC Epitaxial Layers Grown on 4° Off-Axis Si- and C-Face Substrates Using Bistrimethylsilylmethane Precursor. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, N89-N95.	0.9	4
12	Comprehensive Studies on the Carrier Transporting Property and Photo-Bias Instability of Sputtered Zinc Tin Oxide Thin Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 3191-3198.	1.6	16
13	Dynamics of negative bias thermal stress-induced threshold voltage shifts in indium zinc oxide transistors: impact of the crystalline structure on the activation energy barrier. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 165103.	1.3	7
14	Effect of sputter power on the photobias stability of zinc-tin-oxide field-effect transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 011202.	0.6	9
15	Improving the Barrier Height Uniformity of 4H-SiC Schottky Barrier Diodes by Nitric Oxide Post-Oxidation Annealing. <i>IEEE Electron Device Letters</i> , 2014, 35, 868-870.	2.2	15
16	The Anomalous Effect of Oxygen Ratio on the Mobility and Photobias Stability of Sputtered Zinc-Tin-Oxide Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 2071-2077.	1.6	13
17	Reduction in the Interfacial Trap Density of Al <sub>2</sub> O <sub>3</sub> /GaAs Gate Stack by Adopting High Pressure Oxidation. <i>ECS Journal of Solid State Science and Technology</i> , 2014, 3, Q232-Q235.	0.9	1
18	Impact of the Cation Composition on the Electrical Performance of Solution-Processed Zinc Tin Oxide Thin-Film Transistors. <i>ACS Applied Materials &amp; Interfaces</i> , 2014, 6, 14026-14036.	4.0	42

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19	Effects of ZrO <sub>2</sub> doping on HfO <sub>2</sub> resistive switching memory characteristics. Applied Physics Letters, 2014, 105, .	1.5	35
20	Photobias Instability of High Performance Solution Processed Amorphous Zinc Tin Oxide Transistors. ACS Applied Materials & Interfaces, 2013, 5, 3255-3261.	4.0	61
21	Improvement in Photo-Bias Stability of High-Mobility Indium Zinc Oxide Thin-Film Transistors by Oxygen High-Pressure Annealing. IEEE Electron Device Letters, 2013, 34, 894-896.	2.2	52
22	Electrode Engineering for Improving Resistance Switching of Sb <sub>2</sub> O <sub>5</sub> Films. Applied Physics Express, 2013, 6, 091102.	1.1	0
23	Comparison of thermal and atomic-layer-deposited oxides on 4H-SiC after post-oxidation-annealing in nitric oxide. Applied Physics Letters, 2012, 100, .	1.5	20
24	Threshold switching in Si-As-Te thin film for the selector device of crossbar resistive memory. Applied Physics Letters, 2012, 100, .	1.5	44
25	Ti-electrode effects of NiO based resistive switching memory with Ni insertion layer. Applied Physics Letters, 2012, 100, .	1.5	26
26	Anomalous behavior of negative bias illumination stress instability in an indium zinc oxide transistor: A cation combinatorial approach. Applied Physics Letters, 2012, 101, 092107.	1.5	38
27	Concurrent presence of unipolar and bipolar resistive switching phenomena in pnictogen oxide Sb <sub>2</sub> O <sub>5</sub> films. Journal of Applied Physics, 2012, 112, .	1.1	4
28	Growth and electrical properties of silicon oxide grown by atomic layer deposition using Bis(ethyl-methyl-amino)silane and ozone. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	27
29	Improvement of the photo-bias stability of the ZnO/SnO field effect transistors by an ozone treatment. Journal of Materials Chemistry, 2012, 22, 10994.	6.7	76
30	Unipolar resistive switching characteristics of pnictogen oxide films: Case study of Sb <sub>2</sub> O <sub>5</sub> . Journal of Applied Physics, 2012, 112, 104105.	1.1	8
31	Effect of Catalyst Layer Density and Growth Temperature in Rapid Atomic Layer Deposition of Silica Using Tris( <i>tert</i> -pentoxy)silanol. ACS Applied Materials & Interfaces, 2011, 3, 1633-1639.	4.0	20
32	SiO <sub>2</sub> -doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films with high thermal efficiency for applications in phase change random access memory. Nanotechnology, 2011, 22, 254005.	1.3	34
33	Effects of post-oxidation annealing temperature on ZrO <sub>2</sub> thin film deposited on 4H-SiC substrate. Materials Science in Semiconductor Processing, 2011, 14, 13-17.	1.9	27
34	Role of ZrO <sub>2</sub> incorporation in the suppression of negative bias illumination-induced instability in ZnO/SnO thin film transistors. Applied Physics Letters, 2011, 98, .	1.5	59
35	Improvement in the performance of ZnO thin film transistors by using ultralow-pressure sputtering. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 031201.	0.6	1
36	Substrate Dependent Growth Rate of Plasma-Enhanced Atomic Layer Deposition of Titanium Oxide Using N <sub>2</sub> O Gas. Electrochemical and Solid-State Letters, 2010, 13, G13.	2.2	21

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37	Capacitance and Interface Analysis of Transparent Analog Capacitor Using Indium Tin Oxide Electrodes and High-k Dielectrics. Journal of the Electrochemical Society, 2010, 157, G170.	1.3	13
38	Improved 4H-SiC MOS Interface Produced by Oxidized-SiN Gate Oxide. Materials Science Forum, 2010, 645-648, 511-514.	0.3	2
39	Improving the Performance of Tin Oxide Thin-Film Transistors by Using Ultralow Pressure Sputtering. Journal of the Electrochemical Society, 2010, 157, H425.	1.3	9
40	Effects of rapid thermal annealing on Al <sub>2</sub> O <sub>3</sub> /SiN reaction barrier layer/thermal-nitrided SiO <sub>2</sub> stacking gate dielectrics on n-type 4H-SiC. Applied Physics Letters, 2010, 96, .	1.5	8
41	Effect of Postoxidation Annealing on High Temperature Grown SiO <sub>2</sub> /4H-SiC Interfaces. Journal of the Electrochemical Society, 2010, 157, H196.	1.3	15
42	High-Quality Low-Temperature Silicon Oxide by Plasma-Enhanced Atomic Layer Deposition Using a Metal-Organic Silicon Precursor and Oxygen Radical. IEEE Electron Device Letters, 2010, 31, 857-859.	2.2	63
43	Observation of stacking faults formed during homoepitaxial growth of p-type 4H-SiC. Applied Physics Letters, 2009, 94, .	1.5	4
44	Improving the Morphological and Optical Properties of Sputtered Indium Tin Oxide Thin Films by Adopting Ultralow-Pressure Sputtering. Journal of the Electrochemical Society, 2009, 156, J6.	1.3	26
45	The reason for the increased threshold switching voltage of SiO <sub>2</sub> doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films for phase change random access memory. Applied Physics Letters, 2009, 95, 112110.	1.5	16
46	Plasma-Enhanced Atomic Layer Deposition of TiO <sub>2</sub> and Al-Doped TiO <sub>2</sub> Films Using N <sub>2</sub> O and O <sub>2</sub> Reactants. Journal of the Electrochemical Society, 2009, 156, G138.	1.3	46
47	Improved electrical properties of tin-oxide films by using ultralow-pressure sputtering process. Thin Solid Films, 2009, 518, 1170-1173.	0.8	13
48	The Formation of an Almost Full Atomic Monolayer via Surface Modification by N <sub>2</sub> O-Plasma in Atomic Layer Deposition of ZrO <sub>2</sub> Thin Films. Chemistry of Materials, 2009, 21, 4374-4379.	3.2	26
49	Atomic Layer Deposition of Ruthenium Nanoparticles Using a Low-Density Dielectric Film as Template Structure. Chemistry of Materials, 2009, 21, 4006-4011.	3.2	13
50	Influence of Substrates on the Nucleation and Growth Behaviors of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Films by Combined Plasma-Enhanced Atomic Layer and Chemical Vapor Deposition. Chemistry of Materials, 2009, 21, 2386-2396.	3.2	51
51	Effects of heat treatment in vacuum on the physical properties of thermal nitrided silicon dioxide gate on 4H-silicon carbide. Thin Solid Films, 2008, 516, 7921-7924.	0.8	1
52	Current conduction mechanisms in atomic-layer-deposited HfO <sub>2</sub> /nitrided-SiO <sub>2</sub> stacked gate on 4H silicon carbide. Journal of Applied Physics, 2008, 103, .	1.1	121
53	Phase transformation behaviors of SiO <sub>2</sub> doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> films for application in phase change random access memory. Applied Physics Letters, 2008, 92, .	1.5	42
54	Thermal Annealing Effects on the Atomic Layer Deposited LaAlO <sub>3</sub> Thin Films on Si Substrate. Electrochemical and Solid-State Letters, 2008, 11, G33.	2.2	19

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55	The Role of the Methyl and Hydroxyl Groups of Low-k Dielectric Films on the Nucleation of Ruthenium by ALD. <i>Electrochemical and Solid-State Letters</i> , 2008, 11, H210.	2.2	26
56	Enhanced Nucleation Behavior of Atomic-Layer-Deposited Ru Film on Low-k Dielectrics Afforded by UV-O <sub>3</sub> Treatment. <i>Electrochemical and Solid-State Letters</i> , 2008, 11, G5.	2.2	21
57	Homoepitaxial Growth of Vanadium-Doped Semi-insulating 4H-SiC Using Bis-trimethylsilylmethane and Bis-cyclopentadienylvanadium Precursors. <i>Journal of the Electrochemical Society</i> , 2008, 155, H11.	1.3	8
58	Metal-Core Printed Circuit Board With Alumina Layer by Aerosol Deposition Process. <i>IEEE Electron Device Letters</i> , 2008, 29, 991-993.	2.2	48
59	Dependency of threshold switching on density of localized states of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films for phase change random access memory. <i>Applied Physics Letters</i> , 2008, 93, 172114.	1.5	15
60	The effects of (Ba,Sr,Ca)CO <sub>3</sub> or LaB <sub>6</sub> addition on the x-ray photoelectron spectroscopy spectra and electrical properties of the MgO thin films in alternating current plasma display panels. <i>Journal of Materials Research</i> , 2008, 23, 444-451.	1.2	0
61	Electronic Properties of Atomic-Layer-Deposited Al <sub>2</sub> O <sub>3</sub> /Thermal-Nitrided SiO <sub>2</sub> Stacking Dielectric on 4H SiC. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, H69.	2.2	39
62	New DC Arc Discharge Synthesis Method for Carbon Nanotubes Using Xylene Ferrocene as Floating Catalyst. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 1818-1820.	0.8	7
63	Analysis of current conduction mechanisms in atomic-layer-deposited Al <sub>2</sub> O <sub>3</sub> gate on 4H silicon carbide. <i>Applied Physics Letters</i> , 2007, 90, 162113.	1.5	36
64	Deposition Characteristics and Annealing Effect of La <sub>2</sub> O <sub>3</sub> Films Prepared Using La(iPrCp) <sub>3</sub> Precursor. <i>Journal of the Electrochemical Society</i> , 2007, 154, G49.	1.3	18
65	Homoepitaxial Growth of Vanadium-Doped 4H-SiC Using Bis-Trimethylsilylmethane and Verrocene Precursors. <i>Materials Science Forum</i> , 2007, 556-557, 113-116.	0.3	0
66	Improvement of Surface Morphologies of Ru Thin Films by 2-Step MOCVD Process Using (2,4-Demethylpentadienyl)(Ethylcyclopentadienyl)Ruthenium and Oxygen. <i>Solid State Phenomena</i> , 2007, 124-126, 41-44.	0.3	0
67	Effects of Thermally Oxidized-SiN Gate Oxide on 4H-SiC Substrate. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, H327.	2.2	5
68	The Effect of the Dehydration of MgO Films on their XPS Spectra and Electrical Properties. <i>Journal of the Electrochemical Society</i> , 2007, 154, J408.	1.3	22
69	Improvement in Thermal Stability of Stacked Structures of Aluminum Nitride and Lanthanum Oxide Thin Films on Si Substrate. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, G93.	2.2	8
70	Effects of Annealing Condition on Low-k a-SiOC:H Thin Films. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, G11.	2.2	8
71	Electrical Properties of Metal-Oxide-Semiconductor (MOS) Structures on 4H-SiC(0001) Formed by Oxidizing Pre-Deposited Si <sub>x</sub> N <sub>y</sub> . <i>Materials Science Forum</i> , 2007, 556-557, 647-650.	0.3	2
72	Improved Nucleation Behavior of Ru Thin Films Prepared by MOCVD on TiCl <sub>4</sub> Pretreated Substrates. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, D113.	2.2	17

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73	Fabrication of 4H-SiC Schottky barrier diodes with the epilayer grown by Bis-trimethylsilylmethane precursor. , 2007, , .		0
74	Semiempirical method for calculation of secondary electron emission coefficients of insulating materials using their spectra of x-ray photoelectron spectroscopy. Journal of Materials Research, 2007, 22, 3178-3185.	1.2	2
75	The structures of low dielectric constant SiOC thin films prepared by direct and remote plasma enhanced chemical vapor deposition. Thin Solid Films, 2007, 515, 5035-5039.	0.8	25
76	UV-O3 treatment effects on structural changes of low-k thin films. Microelectronic Engineering, 2007, 84, 2188-2191.	1.1	12
77	Heavily nitrogen-doped 4H-SiC homoepitaxial films grown on porous SiC substrates. Journal of Crystal Growth, 2007, 305, 83-87.	0.7	6
78	Improved Electronic Performance of $\text{HfO}_2/\text{SiO}_2$ Stacking Gate Dielectric on 4H SiC. IEEE Transactions on Electron Devices, 2007, 54, 3409-3413.	1.6	38
79	Properties of lanthanum oxide thin films deposited by cyclic chemical vapor deposition using tris(isopropyl-cyclopentadienyl)lanthanum precursor. Journal of Applied Physics, 2006, 100, 024111.	1.1	50
80	P-89: The Effect of Dehydration of MgO Protecting Layer on the XPS Spectra and the Electrical Properties in AC-PDP. Digest of Technical Papers SID International Symposium, 2006, 37, 540.	0.1	1
81	Fabrication and characterization of 4H-SiC planar MESFETs. Microelectronic Engineering, 2006, 83, 160-164.	1.1	41
82	Preparation of carbon nanotubes by DC arc discharge process under reduced pressure in an air atmosphere. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 133, 241-244.	1.7	35
83	The preparation of carbon nanotubes by dc arc discharge using a carbon cathode coated with catalyst. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 130, 73-80.	1.7	25
84	The preparation of carbon nanotubes by DC arc discharge process using Xylene-Ferrocene as a floating catalyst precursor. , 2006, , .		0
85	Electrical Properties of the $\text{La}_{0.2}\text{O}_{0.3}/4\text{H-SiC}$ Interface Prepared by Atomic Layer Deposition Using $\text{La}(\text{iPrCp})_3$ and $\text{H}_{2.2}\text{O}$ . Materials Science Forum, 2006, 527-529, 1083-1086.	0.3	23
86	Property Changes of Aluminum Oxide Thin Films Deposited by Atomic Layer Deposition under Photon Radiation. Journal of the Electrochemical Society, 2006, 153, F87.	1.3	32
87	$\text{SiO}_2$ Incorporation Effects in $\text{Ge}_{0.2}\text{Sb}_{0.2}\text{Te}_{0.5}$ Films Prepared by Magnetron Sputtering for Phase Change Random Access Memory Devices. Electrochemical and Solid-State Letters, 2006, 9, G259.	2.2	46
88	Dopant Penetration Behavior of B-Doped $\text{P}^{+}$ Polycrystalline- $\text{Si}_{0.73}\text{Ge}_{0.27}$ - $\text{Al}_{0.2}\text{O}_3$ or $\text{AlN}/\text{Al}_{0.2}\text{O}_3/\text{n-Si}$ Metal Insulator Semiconductor Capacitors. Electrochemical and Solid-State Letters, 2006, 9, G84.	2.2	1
89	Properties of Aluminum Nitride Thin Films Deposited by an Alternate Injection of Trimethylaluminum and Ammonia under Ultraviolet Radiation. Journal of the Electrochemical Society, 2006, 153, C229.	1.3	31
90	Homoepitaxial growth and electrical characterization of iron-doped semi-insulating 4H-SiC epilayer. Applied Physics Letters, 2006, 89, 152112.	1.5	18

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91	Investigation into the Structural and Electrical Properties of a-SiCO:H as a Diffusion Barrier to Copper. Journal of the Electrochemical Society, 2006, 153, F228.	1.3	15
92	Study on the Step Coverage of Metallorganic Chemical Vapor Deposited TiO[sub 2] and SrTiO[sub 3] Thin Films. Journal of the Electrochemical Society, 2005, 152, C435.	1.3	12
93	Buffer-layer-free growth of high-quality epitaxial GaN films on 4H-SiC substrate by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2005, 276, 407-414.	0.7	17
94	The electrical and physical analysis of Pt gate/Al <sub>2</sub> O <sub>3</sub> /p-Si (100) with dual high-k gate oxide thickness for deep submicron complementary metal-oxide-semiconductor device with low power and high reliability. Journal of Electronic Materials, 2005, 34, 1104-1109.	1.0	4
95	Pt-Doped Ru Films Prepared by CVD as Electrodes for DRAM Capacitors. Electrochemical and Solid-State Letters, 2005, 8, C12.	2.2	5
96	Study on the Synthesis of Carbon Nanotubes using the Catalyst Metal Deposited Carbon Cathode Electrode in a DC Arc Discharge Process. Materials Research Society Symposia Proceedings, 2005, 900, 1.	0.1	0
97	Improvements in Growth Behavior of CVD Ru Films on Film Substrates for Memory Capacitor Integration. Journal of the Electrochemical Society, 2005, 152, C15.	1.3	44
98	Relationship between the microstructure and the discharge characteristics of MgO protecting layer in alternating current plasma display panels. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1162-1166.	0.9	18
99	BORON DIFFUSION PROPERTIES AND ELECTRICAL CHARACTERISTICS OF p+ Poly-Si <sub>0.73</sub> Ge <sub>0.27</sub> /Al <sub>x</sub> O <sub>3</sub> /Al <sub>x</sub> N <sub>x</sub> /n-Si (100) USING IN-SITU ALD. Integrated Ferroelectrics, 2005, 74, 79-85.	0.3	0
100	Effect of stress and density on the electrical and physical properties of MgO protecting layer for alternating current-plasma display panels. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1192-1196.	0.9	12
101	Investigation of Ru/TiN Bottom Electrodes Prepared by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2004, 43, 6635-6639.	0.8	7
102	Nitrogen incorporation engineering and electrical properties of high-k gate dielectric (HfO <sub>2</sub> ) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1838.	1.6	29
103	Phosphorus ion implantation and POCl <sub>3</sub> doping effects of n+-polycrystalline-silicon/high-k gate dielectric (HfO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> ) films. Applied Physics Letters, 2004, 84, 2868-2870.	1.5	3
104	Improvement in the Crystalline Quality of Epitaxial GaN Films Grown by MOCVD by Adopting Porous 4H-SiC Substrate. Electrochemical and Solid-State Letters, 2004, 7, C43.	2.2	19
105	Homoepitaxial Growth of Al-Doped 4H-SiC Using Bis-Trimethylsilylmethane Precursor. Materials Science Forum, 2004, 457-460, 233-236.	0.3	0
106	Fabrication and Characterization of 4H-SiC Planar MESFET Using Ion- Implantation. Materials Science Forum, 2004, 457-460, 1181-1184.	0.3	4
107	Growth of GaN Films on Porous 4H-SiC Substrate by Metal-Organic Chemical Vapor Deposition. Materials Science Forum, 2004, 457-460, 1597-1600.	0.3	0
108	Characterization of Undoped and Nitrogen-Doped 4H-SiC Thin Films by CVD from Bis(trimethylsilylmethane) Precursor. Journal of the Electrochemical Society, 2004, 151, G252.	1.3	9

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109	Microstructural characterization of sputter-deposited Pt thin film electrode. Journal of Materials Research, 2004, 19, 460-468.	1.2	9
110	Changes in structures and electrical conduction mechanisms of chemical vapor deposited Ta <sub>2</sub> O <sub>5</sub> thin films by annealing under O <sub>3</sub> atmosphere with ultraviolet light radiation. Journal of Materials Research, 2004, 19, 1516-1523.	1.2	6
111	Comparison of the Electrical Properties of High-k Gate Dielectric (HfO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> ) Films with Pt or n+-Polycrystalline-Silicon Gate. Integrated Ferroelectrics, 2004, 67, 49-57.	0.3	2
112	Effects of surface roughness of substrates on the c-axis preferred orientation of ZnO films deposited by r.f. magnetron sputtering. Thin Solid Films, 2003, 423, 262-266.	0.8	66
113	Deposition of ZnO thin films by magnetron sputtering for a film bulk acoustic resonator. Thin Solid Films, 2003, 435, 179-185.	0.8	107
114	Hydration of r.f. magnetron sputtered MgO thin films for a protective layer in AC plasma display panel. Thin Solid Films, 2003, 435, 95-101.	0.8	49
115	Characterization of low-dielectric-constant SiOC thin films deposited by PECVD for interlayer dielectrics of multilevel interconnection. Surface and Coatings Technology, 2003, 171, 39-45.	2.2	59
116	Electrical reliability of highly reliable 256M-bit mobile DRAM with top-edge round STI and dual gate oxide. Microelectronics Reliability, 2003, 43, 735-739.	0.9	1
117	The protection of MgO film against hydration by using Al <sub>2</sub> O <sub>3</sub> capping layer deposited by magnetron sputtering method. Thin Solid Films, 2003, 435, 199-204.	0.8	30
118	Deposition and Characterization of High Dielectric Thin Films for Memory Device Application. Surface Review and Letters, 2003, 10, 591-604.	0.5	2
119	Hydration behavior of MgO single crystals and thin films. Journal of Materials Research, 2003, 18, 2895-2903.	1.2	36
120	Investigation of interface trap states in TiN/Al <sub>2</sub> O <sub>3</sub> /p-Si capacitor by deep level transient spectroscopy. Applied Physics Letters, 2003, 82, 1066-1068.	1.5	28
121	Analysis of stresses in Ru thin films prepared by chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1381-1385.	0.9	5
122	Arsenic penetration behavior and electrical characteristics of As-doped n+ polycrystalline-silicon/high-k gate dielectric (HfO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> ) films on Si (100) substrate. Applied Physics Letters, 2003, 83, 1403-1405.	1.5	12
123	Characterization of 4H-SiC Homoepitaxial Films on Porous 4H-SiC from Bis(trimethylsilyl)methane Precursor. Journal of the Electrochemical Society, 2003, 150, G90.	1.3	4
124	Deep Submicron CMOS Technology Using Top-Edge Round STI and Dual Gate Oxide for Low Power 256 M-Bit Mobile DRAM. Japanese Journal of Applied Physics, 2003, 42, 1892-1896.	0.8	5
125	Dependence of ferroelectric performance of sol-gel-derived Pb(Zr,Ti)O <sub>3</sub> thin films on bottom-Pt-electrode thickness. Applied Physics Letters, 2002, 81, 3224-3226.	1.5	17
126	Metallorganic Chemical Vapor Deposition of Ru Films Using Cyclopentadienyl-Propylcyclopentadienylruthenium(II) and Oxygen. Journal of the Electrochemical Society, 2002, 149, C317.	1.3	30



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127	Low Temperature 4H-SiC Epitaxial Growth on 4H-SiC (112̄,0) and (11̄,00) Faces by Organometallic Chemical Vapor Deposition. Journal of the Electrochemical Society, 2002, 149, G526.	1.3	7
128	Cation Composition Control of MOCVD (Ba,Sr)TiO <sub>3</sub> Thin Films along the Capacitor Hole. Journal of the Electrochemical Society, 2002, 149, G585.	1.3	33
129	Effect of Top Electrode Deposition Condition on Polarization Fatigue of RuO <sub>2</sub> /Pb(Zr,Ti)O <sub>3</sub> /RuO <sub>2</sub> Thin Film Capacitors. Journal of the Electrochemical Society, 2002, 149, F152.	1.3	2
130	Low Power CMOS Process Technologies and Characteristics for advanced High Density Mobile DRAM. , 2002, , .		1
131	Infrared spectroscopy study of low-dielectric-constant fluorine-incorporated and carbon-incorporated silicon oxide films. Journal of Applied Physics, 2001, 90, 3367-3370.	1.1	154
132	Effects of substrates roughness on c-axis preferred orientation of ZnO films deposited by rf magnetron sputtering. Materials Research Society Symposia Proceedings, 2001, 672, 1.	0.1	1
133	Deposition and Characterization of PECVD SiOC Films by Using Bistrimethylsilylmethane (BTMSM) Precursor. Materials Research Society Symposia Proceedings, 2001, 714, 7121.	0.1	1
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